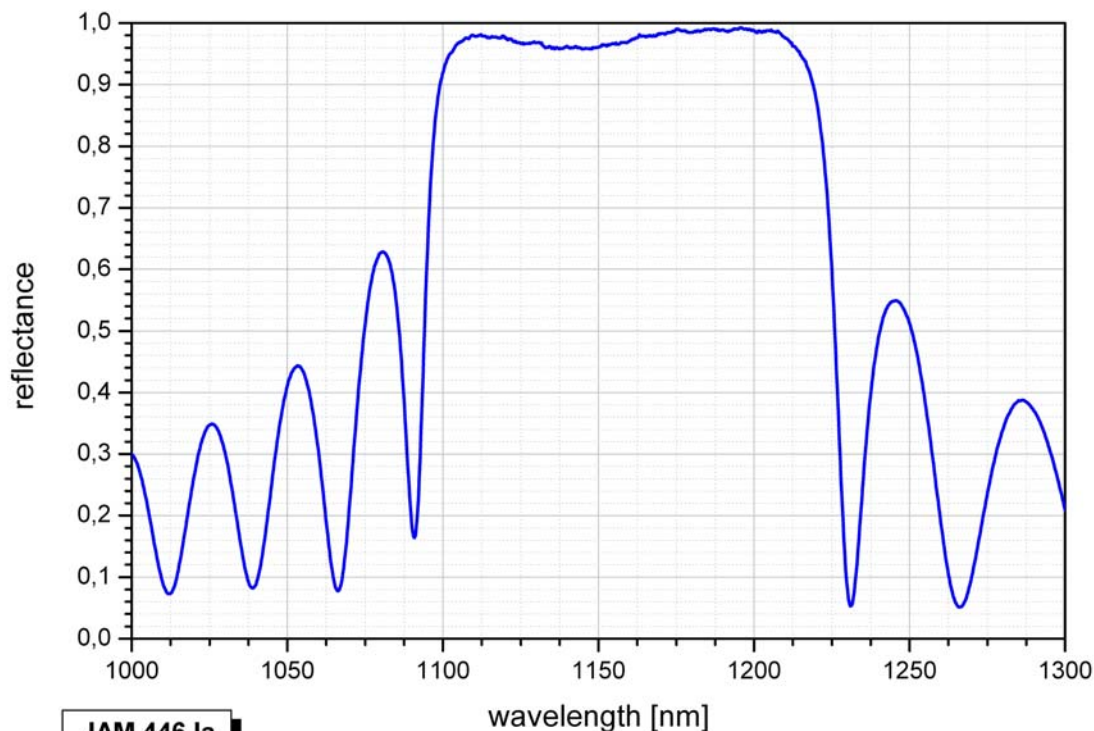


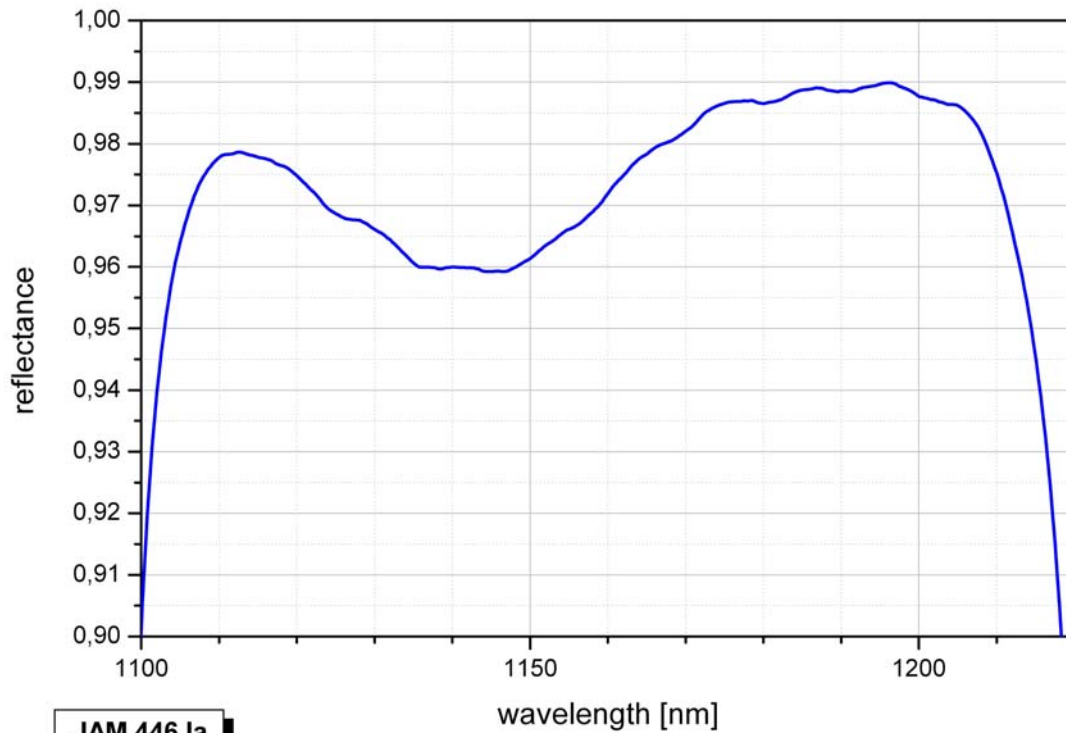
SAM™ data sheet SAM-1150-4-x, $\lambda = 1150 \text{ nm}$

Laser wavelength	$\lambda = 1150 \text{ nm}$
High reflection band (R > 96%)	$\lambda = 1110 \dots 1200 \text{ nm}$
Absorptance	$A_0 = 4 \%$
Saturation fluence	$\Phi_{\text{sat}} = 70 \mu\text{J}/\text{cm}^2$
Relaxation time constant	$\tau \sim 500 \text{ fs}$
Modulation depth	$\Delta R = 2.5 \%$
Chip area	4mm x 4mm; other dimensions on request
Chip thickness	400 μm ; optional: 150 μm on request
Protection	the SAM is protected with a dielectric front layer
Mounting of SAM-1150-4-x	denotes the type of mounting as follows:
$x = 0$	unmounted
$x = 12.7 \text{ g}$	glued on a gold plated Cu-cylinder with 12.7 mm \varnothing
$x = 25.4 \text{ g}$	glued on a gold plated Cu-cylinder with 25.4 mm \varnothing
$x = 12.7 \text{ s}$	soldered on a gold plated Cu-cylinder with 12.7 mm \varnothing
$x = 25.4 \text{ s}$	soldered on a gold plated Cu-cylinder with 25.4 mm \varnothing

Low intensity spectral reflectance



JAM 446 Ia



JAM 446 la